

## Transistors

Order code	Manufacturer code	Description
81-0228	n/a	ZTX689B 20V NPN HIGH GAIN POWER TRANS

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The enclosed information is believed to be correct, Information may change 'without notice' due to product improvement. Users should ensure that the product is suitable for their use. E. & O. E.	Revision A 04/07/2003

# NPN SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

## ZTX689B

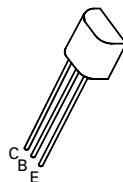
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### FEATURES

- \* 20 Volt  $V_{CEO}$
- \* Gain of 400 at  $I_C=2$  Amps
- \* Very low saturation voltage

### APPLICATIONS

- \* Darlington replacement
- \* Flash gun convertors
- \* Battery powered circuits
- \* Motor drivers



**E-Line**  
**TO92 Compatible**

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	20	V
Collector-Emitter Voltage	$V_{CEO}$	20	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Peak Pulse Current	$I_{CM}$	8	A
Continuous Collector Current	$I_C$	3	A
Practical Power Dissipation*	$P_{totp}$	1.5	W
Power Dissipation at $T_{amb}=25^{\circ}C$ derate above $25^{\circ}C$	$P_{tot}$	1 5.7	W mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^{\circ}C$

\*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ )

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	20			V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	20			V	$I_C=10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu A$
Collector Cut-Off Current	$I_{CBO}$			0.1	$\mu A$	$V_{CB}=16V$
Emitter Cut-Off Current	$I_{EBO}$			0.1	$\mu A$	$V_{EB}=4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.1 0.5	V	$I_C=0.1A, I_B=0.5mA^*$ $I_C=2A, I_B=10mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			0.9	V	$I_C=1A, I_B=10mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			0.9	V	$I_C=1A, V_{CE}=2V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	500 400 150				$I_C=0.1A, V_{CE}=2V^*$ $I_C=2A, V_{CE}=2V^*$ $I_C=6A, V_{CE}=2V^*$

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## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ )

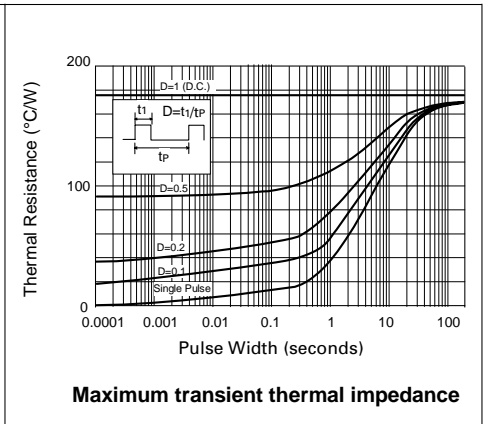
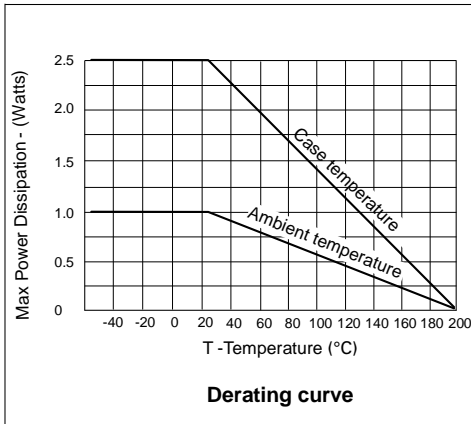
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Transition Frequency	$f_T$	150			MHz	$I_C=50\text{mA}$ , $V_{CE}=5\text{V}$ $f=50\text{MHz}$
Input Capacitance	$C_{ibo}$		200		pF	$V_{EB}=0.5\text{V}$ , $f=1\text{MHz}$
Output Capacitance	$C_{obo}$		16		pF	$V_{CB}=10\text{V}$ , $f=1\text{MHz}$
Switching Times	$t_{on}$		30		ns	$I_C=500\text{mA}$ , $I_{B1}=50\text{mA}$ $I_{B2}=50\text{mA}$ , $V_{CC}=10\text{V}$
	$t_{off}$		800		ns	

\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

## THERMAL CHARACTERISTICS

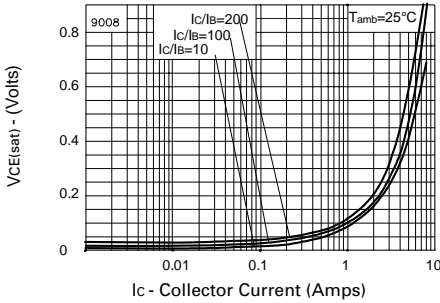
PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient <sub>1</sub>	$R_{th(j-amb)1}$	175	$^{\circ}\text{C/W}$
Junction to Ambient <sub>2</sub>	$R_{th(j-amb)2} \dagger$	116	$^{\circ}\text{C/W}$
Junction to Case	$R_{th(j-case)}$	70	$^{\circ}\text{C/W}$

$\dagger$  Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.

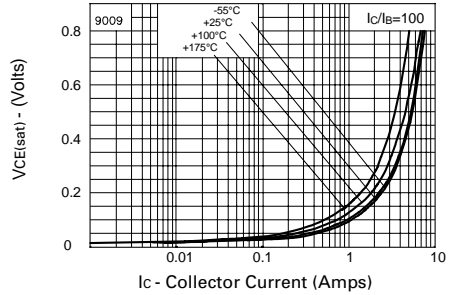


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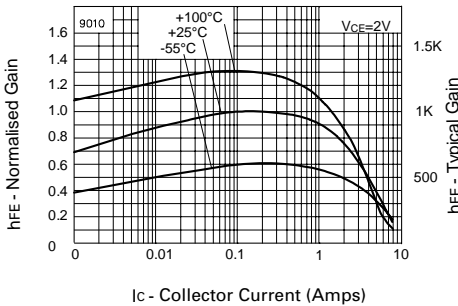
## TYPICAL CHARACTERISTICS



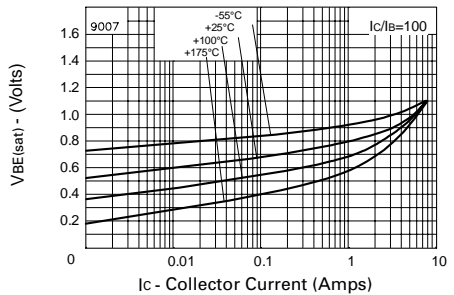
**$V_{CE(sat)}$  v  $I_C$**



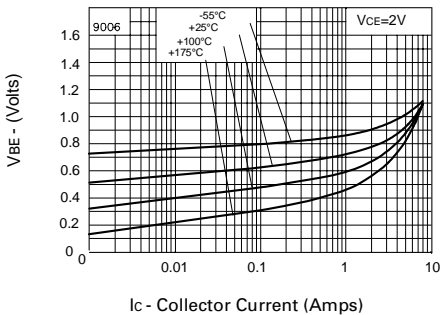
**$V_{CE(sat)}$  v  $I_C$**



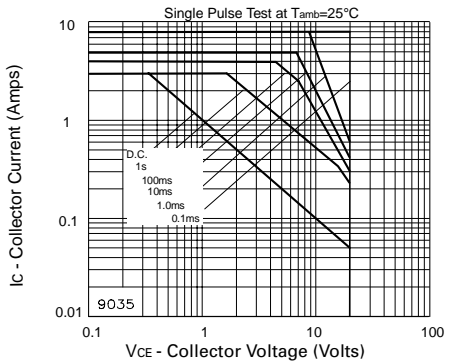
**$h_{FE}$  v  $I_C$**



**$V_{BE(sat)}$  v  $I_C$**



**$V_{BE(on)}$  v  $I_C$**



**Safe Operating Area**